

DSA2507

Silicon PNP epitaxial planar type

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-20	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-1.5	A
Peak collector current	I_{CP}	-5	A
Collector power dissipation *	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Printed circuit board: Copper foil area of 2.25 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Package

- Code
Mini3-G3-B
- Pin Name
 1. Base
 2. Emitter
 3. Collector

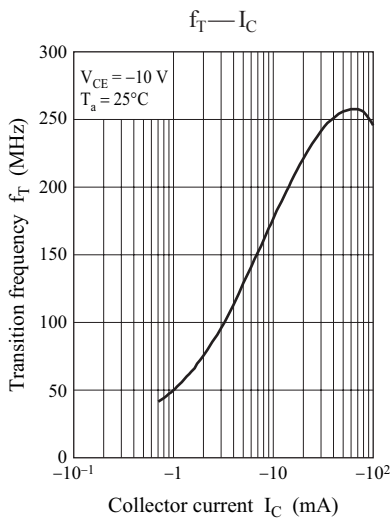
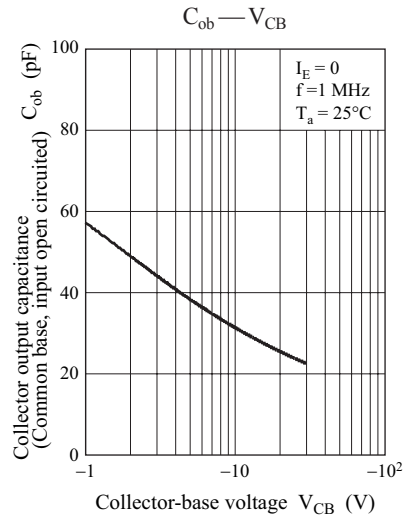
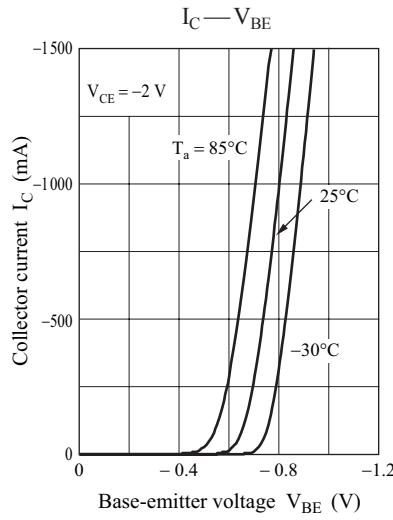
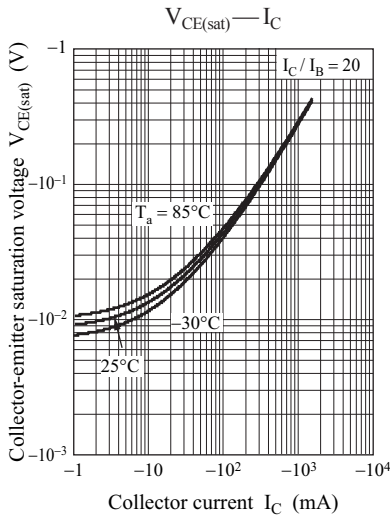
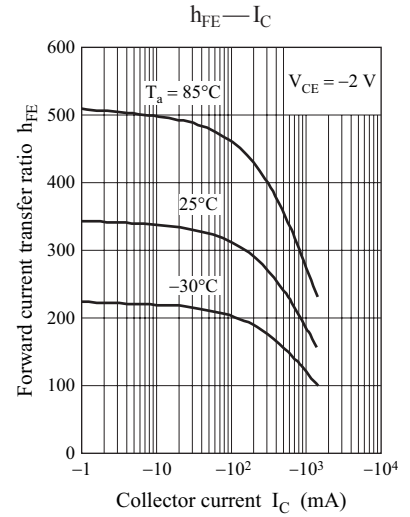
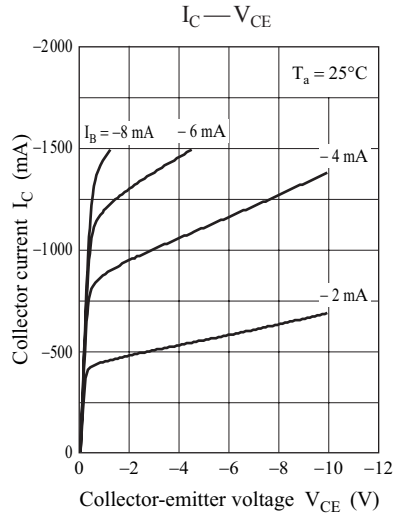
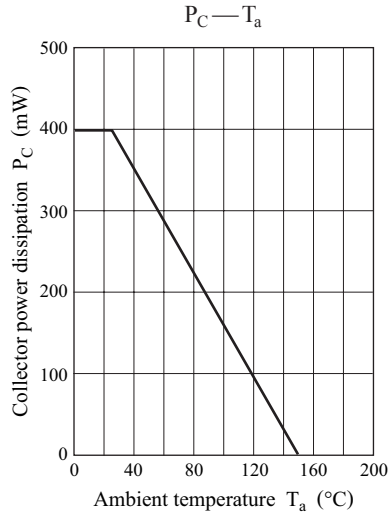
■ Marking Symbol: B4

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Forward current transfer ratio *	h_{FE}	$V_{CE} = -2 \text{ V}, I_C = -100 \text{ mA}$	160		560	—
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -500 \text{ mA}, I_B = -25 \text{ mA}$		-50	-150	mV
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -20 \text{ mA}$		220		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			35	pF

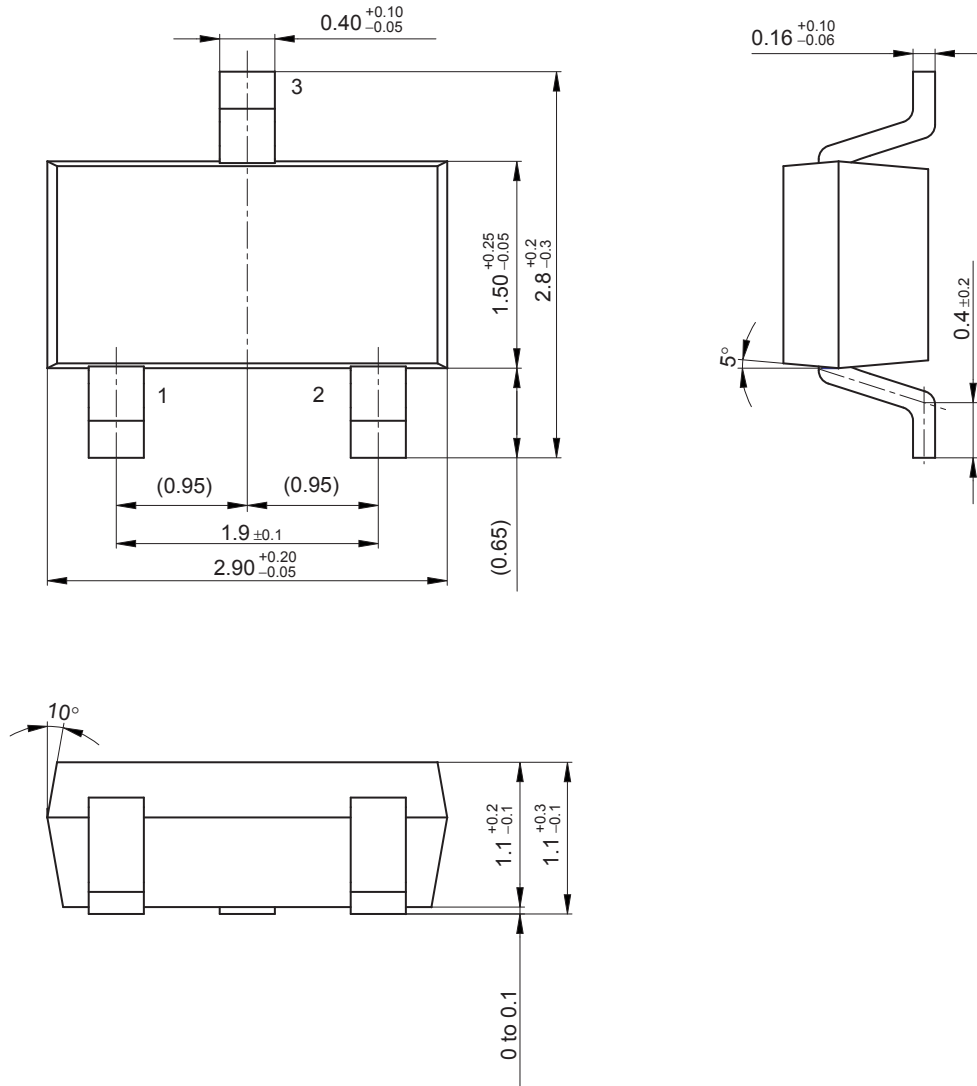
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement



Mini3-G3-B

Unit: mm



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